

MOS Field Effect Power Transistors
2SK2723

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

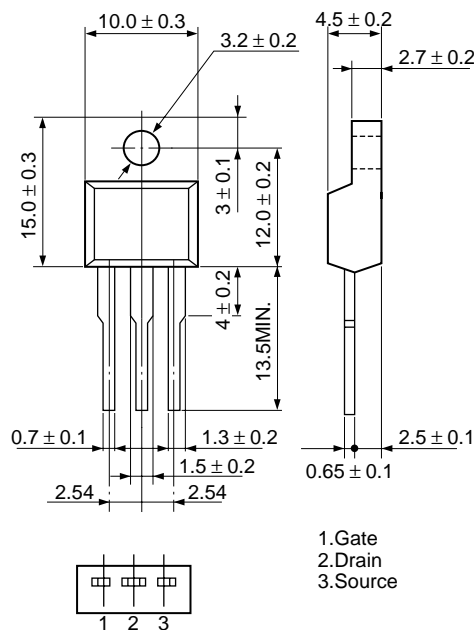
DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Low On-Resistance
 $R_{DS(on)1} = 40m\Omega$ Max. ($V_{GS} = 10V, I_D = 13A$)
 $R_{DS(on)2} = 60m\Omega$ Max. ($V_{GS} = 4V, I_D = 13A$)
- Low C_{iss} $C_{iss} = 830pF$ Typ.
- Built-in G-S Protection Diode
- Isolated TO-220 Package

PACKAGE DIMENSIONS
(in millimeter)

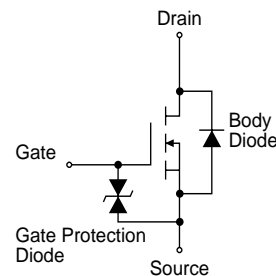


MP-45F (ISOLATED TO-220)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$)

Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	$I_D(DC)$	± 25	A
Drain Current (pulse)*	$I_D(pulse)$	± 100	A
Total Power Dissipation ($T_A = 25^\circ C$)	P_T	2.0	W
Total Power Dissipation ($T_c = 25^\circ C$)	P_T	25	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10 \mu s, Duty\ Cycle \leq 1\%$



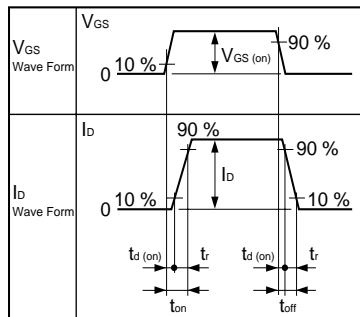
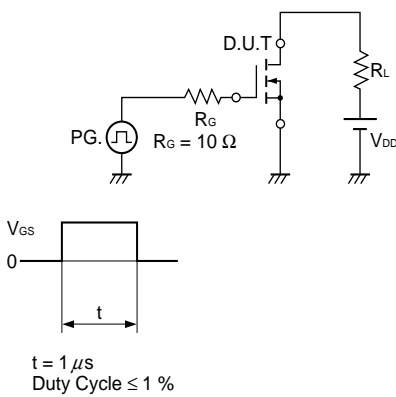
The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device acutally used, an additional protection circiut is externally required if voltage exceeding the rated voltage may be applied to this device.

The information in this document is subject to change without notice.

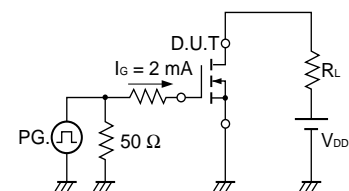
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS (on) 1}	V _{GS} = 10 V, I _D = 13 A		28	40	mΩ
	R _{DS (on) 2}	V _{GS} = 4 V, I _D = 13 A		45	60	mΩ
Gate to Source Cutoff Voltage	V _{GS (off)}	V _{DS} = 10 V, I _D = 1 mA	1.0	1.6	2.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 13 A	8.0	18		S
Drain Leakage Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz		830		pF
Output Capacitance	C _{oss}			430		pF
Reverse Transfer Capacitance	C _{rss}			185		pF
Turn-On Delay Time	t _{d (on)}	I _D = 13 A V _{GS (on)} = 10 V		21		ns
Rise Time	t _r			185		ns
Turn-Off Delay Time	t _{d (off)}	V _{DD} = 30 V R _G = 10 Ω		100		ns
Fall Time	t _f			110		ns
Total Gate Charge	Q _G	I _D = 25 A V _{DD} = 48 V V _{GS} = 10 V		35		nC
Gate to Source Charge	Q _{GS}			2.8		nC
Gate to Drain Charge	Q _{GD}			15		nC
Body Diode Forward Voltage	V _{F (S-D)}	I _F = 25 A, V _{GS} = 0		1.0		V
Reverse Recovery Time	t _{r r}	I _F = 25 A, V _{GS} = 0 di/dt = 100 A/μs		60		ns
Reverse Recovery Charge	Q _{r r}			125		nC

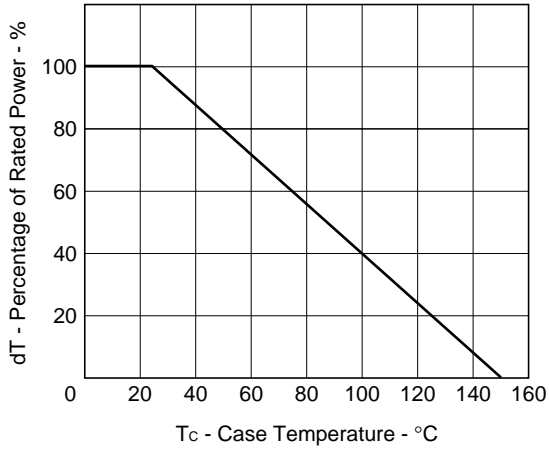
Test Circuit 1 Switching Time



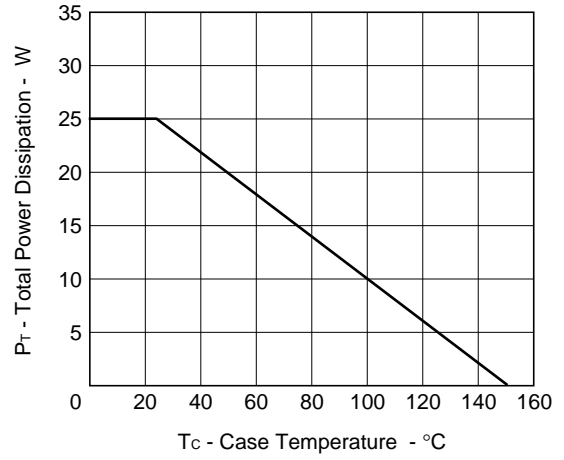
Test Circuit 2 Gate Charge



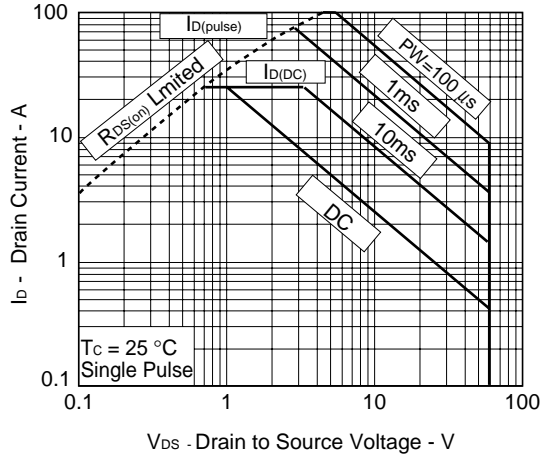
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



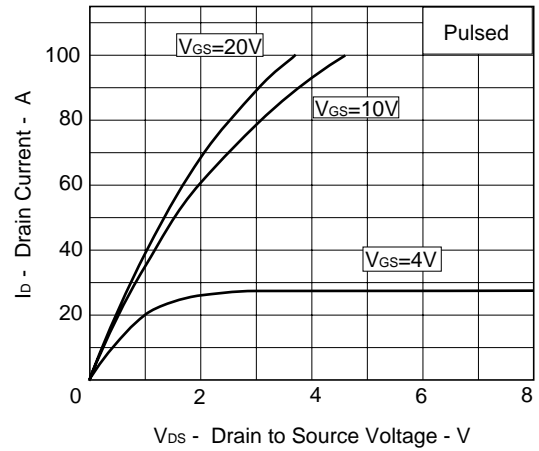
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



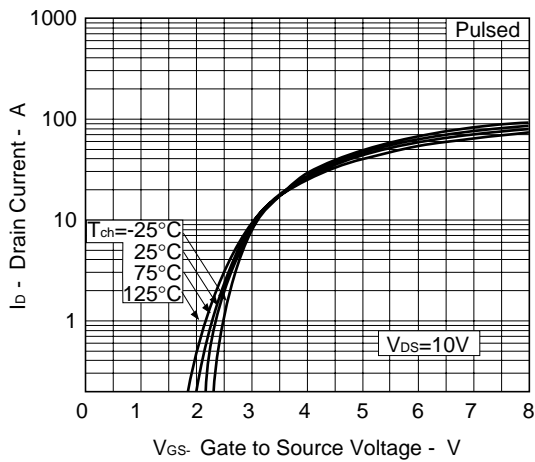
FORWARD BIAS SAFE OPERATING AREA



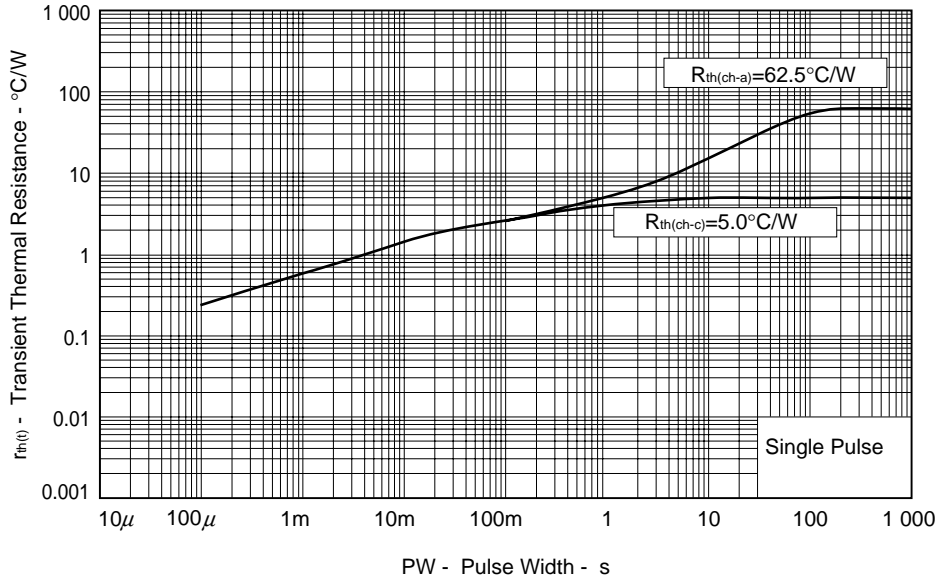
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



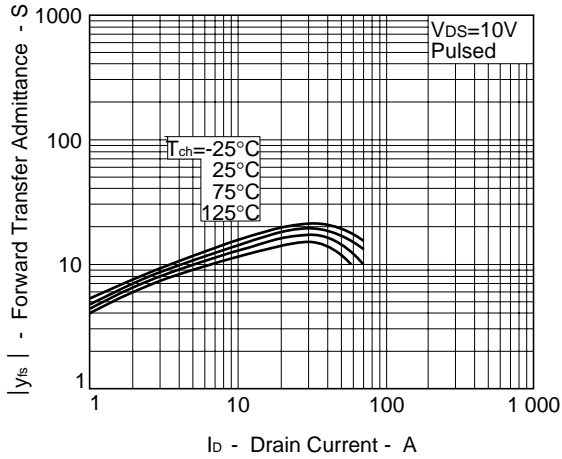
FORWARD TRANSFER CHARACTERISTICS



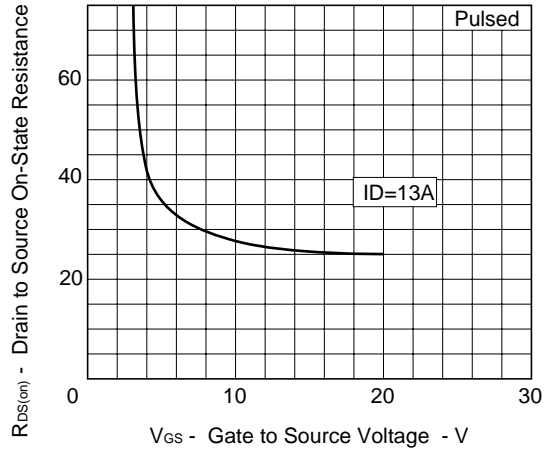
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



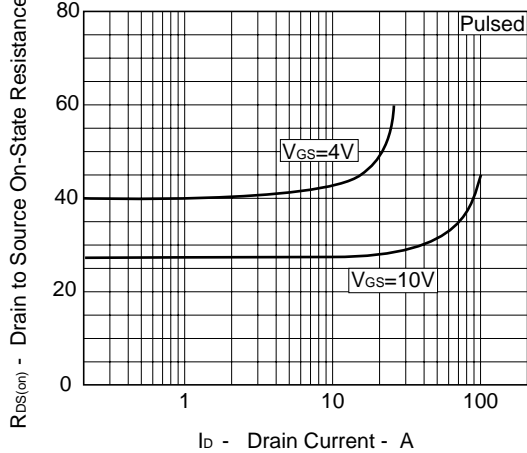
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



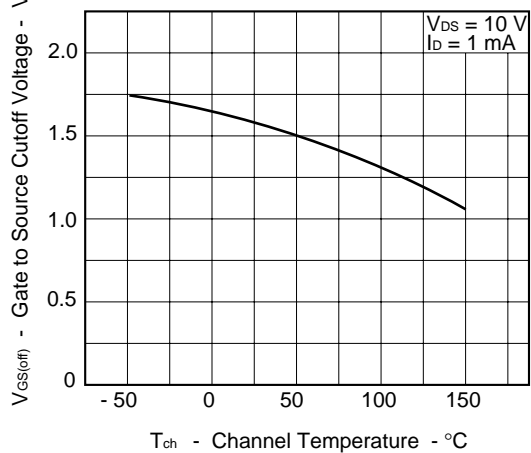
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



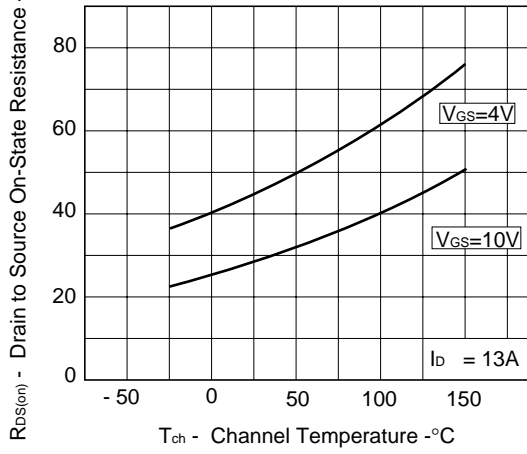
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



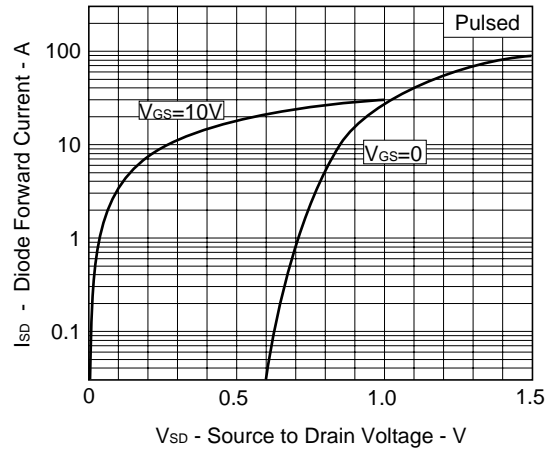
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



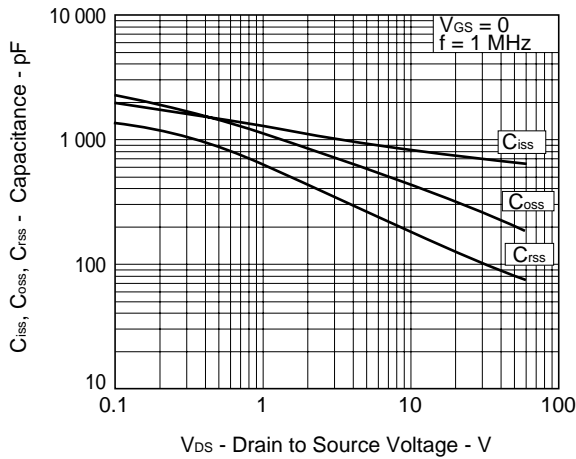
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



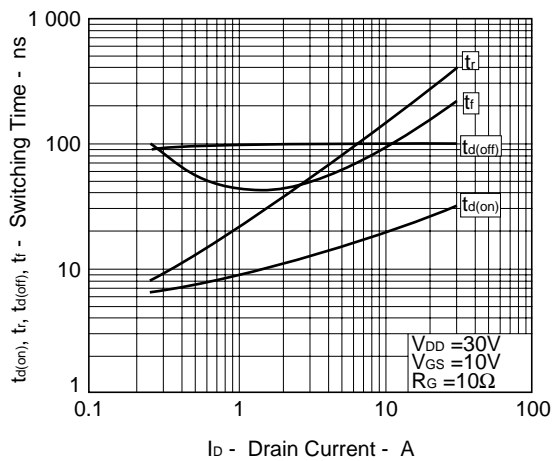
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



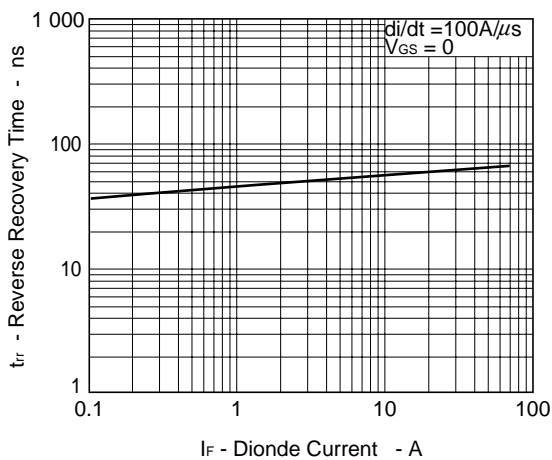
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



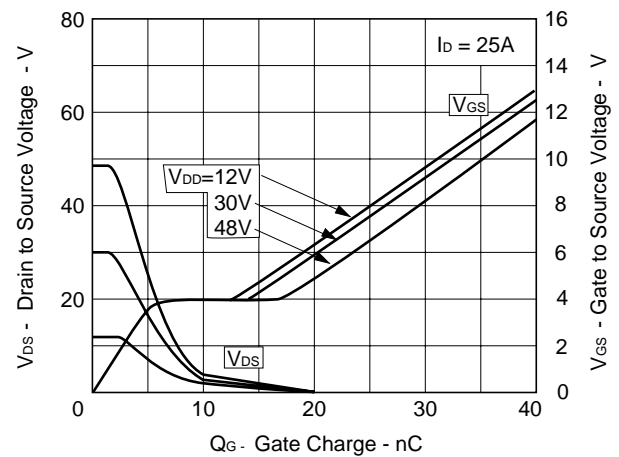
SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DIODE CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	C10535E
Semiconductor device package manual.	C10943X
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	X10679E
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037

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Anti-radioactive design is not implemented in this product.